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N-Channel 55 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^d	Q _g (Typ.)		
55	0.0063 at $V_{GS} = 10 \text{ V}$	110	87		
35	0.0071 at $V_{GS} = 4.5 \text{ V}$	90			

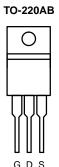
FEATURES

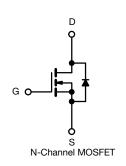
- DT-Trench Power MOSFET
- 100 % R_q and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- Power Supply
 - Secondary Synchronous Rectification
- DC/DC Converter





ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unless other	erwise noted)			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	55	V	
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	I _D	110 ^d	A	
	T _C = 70 °C	טי	90 ^d		
Pulsed Drain Current		I _{DM}	330		
Avalanche Current		I _{AS}	60		
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	180	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	Р	125 ^b	W	
	T _A = 25 °C ^c	- P _D	3.1		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)	R _{thJC}	1	- *C/VV	

Notes:

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Package limited.





Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	55			V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		4	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA
Zero Gate Voltage Drain Current		V _{DS} = 55 V, V _{GS} = 0 V			1	μΑ
	I _{DSS}	V _{DS} = 55 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 55 V, V _{GS} = 0 V, T _J = 150 °C			250	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	50			Α
Drain-Source On-State Resistance ^a		$V_{GS} = 10 \text{ V}, I_D = 22 \text{ A}$		0.0063		Ω
	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$		0.0071		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		169		S
Dynamic ^b						
Input Capacitance	C _{iss}			5286		pF
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$		705		
Reverse Transfer Capacitance	C _{rss}			283		
Total Gate Charge ^c	Q_g	V _{DS} = 20 V, V _{GS} = 10 V, I _D = 20 A		87	131	nC
Gate-Source Charge ^c	Q_{gs}			15.3		
Gate-Drain Charge ^c	Q_{gd}			12.2		
Gate Resistance	R_{g}	f = 1 MHz	0.5	2.7	5.4	Ω
Turn-On Delay Time ^c	t _{d(on)}			11	20	
Rise Time ^c	t _r	$V_{DD} = 20 \text{ V}, R_L = 2 \Omega$		7	14	- ns
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		45	68	
Fall Time ^c	t _f			7	14	
Drain-Source Body Diode Ratings ar	nd Characteris	stics T _C = 25 °C ^b				
Continuous Current	I _S				110	
Pulsed Current	I _{SM}				330	Α
Forward Voltage ^a	V _{SD}	I _F = 10 A, V _{GS} = 0 V		0.72	1.2	V
Reverse Recovery Time	t _{rr}			42	63	ns
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = 10 A, dl/dt = 100 A/μs		2.5	3.8	Α
Reverse Recovery Charge	Q _{rr}			52	78	nC

Notes:

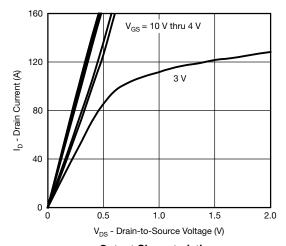
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$ b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

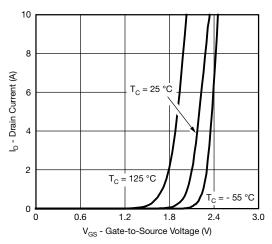




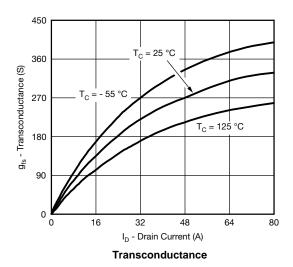
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

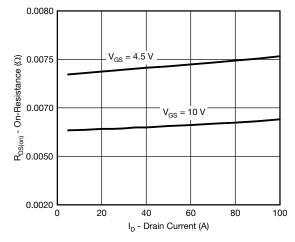


Output Characteristics

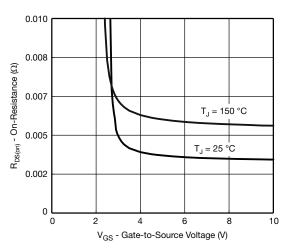


Transfer Characteristics

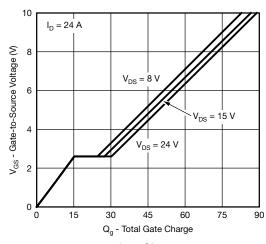




On-Resistance vs. Drain Current



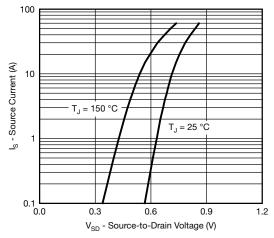
On-Resistance vs. Gate-to-Source Voltage



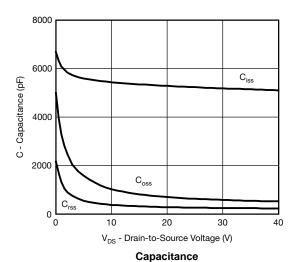
Gate Charge



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

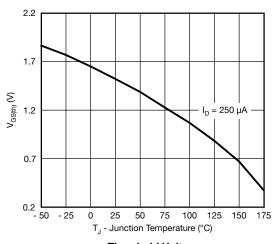


Source-Drain Diode Forward Voltage

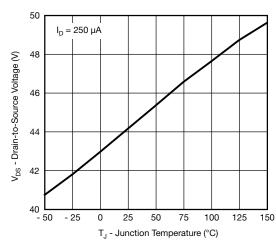


 $\label{eq:TJ-Junction} T_{J} \text{ - Junction Temperature (°C)}$ On-Resistance vs. Junction Temperature

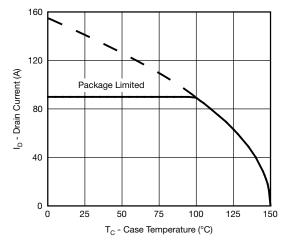
75 100 125 150 175



Threshold Voltage



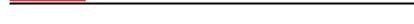
Drain Source Breakdown vs. Junction Temperature



Current Derating

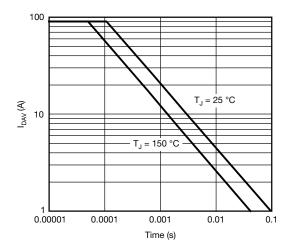
2.0

0.5 - 50 - 25

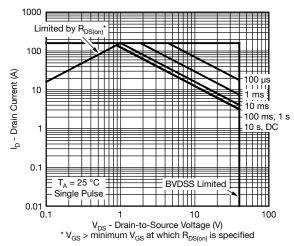


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

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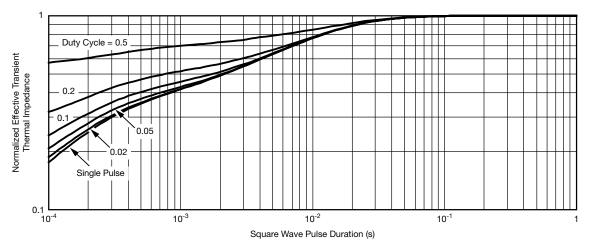


Din-Tek SEMICONDUCTOR



Single Pulse Avalanche Current Capability vs. Time





Normalized Thermal Transient Impedance, Junction-to-Case





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